

# **MOSFET** – Power, P-Channel

-60 V, 6.5 mΩ, -100 A

# **ATP304**

#### **Features**

- ON-Resistance  $R_{DS(on)1} = 5.0 \text{ m}\Omega \text{ (typ)}$
- Input Capacitance Ciss = 13000 pF (typ)
- 4.5 V Drive
- This Device is Pb-Free, Halogen Free and RoHS Compliant

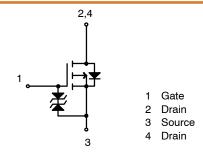
## MAXIMUM RATINGS (Ta = 25°C) (Note 1)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DSS}$	-60	٧
Gate-to-Source Voltage	$V_{GSS}$	±20	V
Drain Current (DC)	I <sub>D</sub>	-100	Α
Drain Current (Pulse) PW ≤ 10 μs, duty cycle ≤ 1%	I <sub>DP</sub>	-400	Α
Allowable Power Dissipation Tc = 25°C	P <sub>D</sub>	90	W
Channel Temperature	T <sub>ch</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C
Avalanche Energy (Single Pulse) (Note 1)	E <sub>AS</sub>	656	mJ
Avalanche Current (Note 2)	I <sub>AV</sub>	-75	Α

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1.  $V_{DD} = -36 \text{ V}$ ,  $L = 100 \mu\text{H}$ ,  $I_{AV} = -75 \text{ A}$  (Figure 1)
- 2. L≤ 100 μH, Single pulse

V <sub>DSS</sub>	R <sub>DS(ON)</sub> MAX	I <sub>D</sub> MAX
-60 V	6.5 mΩ @ –10 V	-100 A
	8.9 mΩ @ -4.5 V	-100 A



#### **ELECTRICAL CONNECTION P-CHANNEL**



DPAK (Single Gauge) / ATPAK CASE 369AM

#### MARKING DIAGRAM



ATP304 = Specific Device Code
Y = Year of Production
M = Assembly Operation Month
W = Work Week in the Month

#### **ORDERING INFORMATION**

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

# **ELECTRICAL CHARACTERISTICS** ( $T_J = 25^{\circ}C$ unless otherwise specified)

				Value		
Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	$I_D = -1$ mA, $V_{GS} = 0$ V	-60	-	-	V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -60 V, V <sub>GS</sub> = 0 V	-	-	-10	μΑ
Gate to Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = +16 V, V <sub>DS</sub> = 0 V	_	_	+10	μΑ
Cutoff Voltage	V <sub>GS</sub> (off)	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1 mA	-1.2	_	-2.6	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -50 A	-	100	-	S
Static Drain to Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> = -50 A, V <sub>GS</sub> = -10 V	_	5.0	6.5	mΩ
	R <sub>DS</sub> (on)2	I <sub>D</sub> = -50 A, V <sub>GS</sub> = -4.5 V	_	6.4	8.9	mΩ
Input Capacitance	Ciss	V <sub>DS</sub> = -20 V, f = 1 MHz	_	13000	_	pF
Output Capacitance	Coss	1	_	1080	-	pF
Reverse Transfer Capacitance	Crss	1	_	760	_	pF
Turn-ON Delay Time	t <sub>d</sub> (on)	(Figure 2)	_	80	-	ns
Rise Time	t <sub>r</sub>	1	_	650	_	ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	1	_	780	_	ns
Fall Time	t <sub>f</sub>	1	_	460	-	ns
Total Gate Charge	Qg	$V_{DS} = -36 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -100 \text{ A}$	_	250	_	nC
Gate to Source Charge	Qgs	1	_	55	-	nC
Gate to Drain "Miller" Charge	Qgd	1	-	50	-	nC
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> = -100 A, V <sub>GS</sub> = 0 V	_	-1.0	-1.5	V
Reverse Recovery Time	t <sub>rr</sub>	(Figure 3)	_	90	-	ns
Reverse Recovery Charge	Q <sub>rr</sub>	$I_S = -100 \text{ A}, V_{GS} = 0 \text{ V}, \text{ di/dt} = -100 \text{ A} / \mu \text{s}$	_	245	-	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

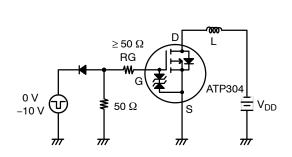


Figure 1. Unclamped Inductive Switching Test Circuit

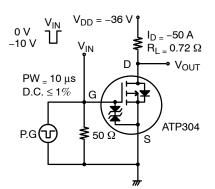


Figure 2. Switching Time Test Circuit

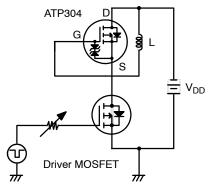
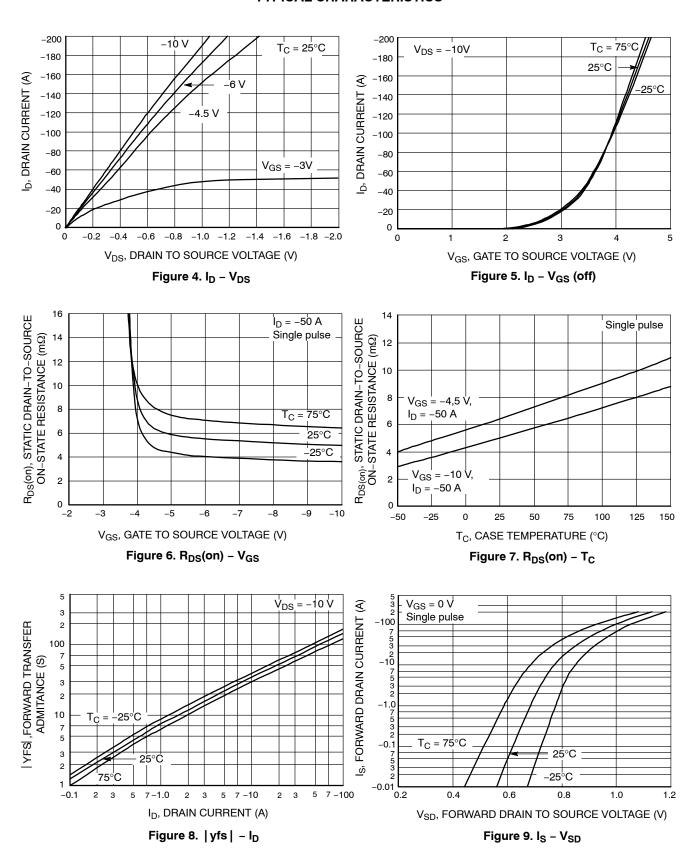


Figure 3. Reserve Recovery Time Test Circuit

#### **TYPICAL CHARACTERISTICS**



#### TYPICAL CHARACTERISTICS (CONTINUED)

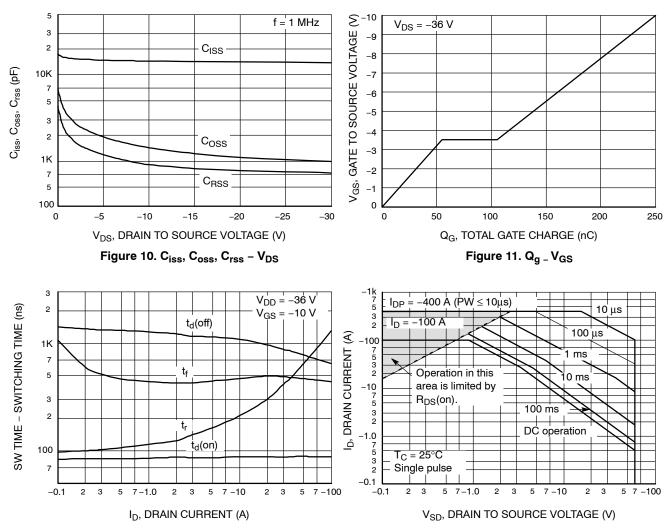
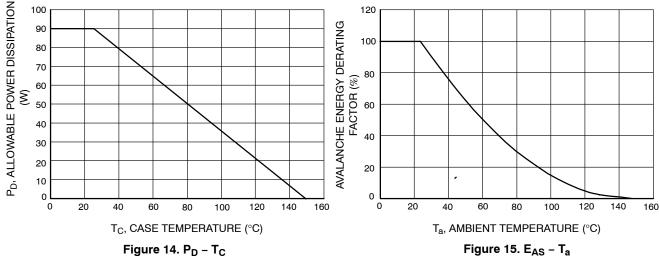


Figure 12. SW Time - ID

Figure 13. SOA



# TYPICAL CHARACTERISTICS (CONTINUED)

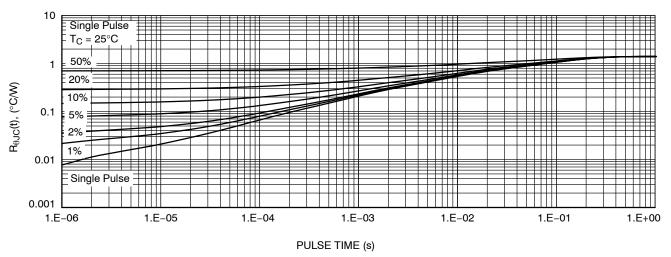


Figure 16. Thermal Response

## **DEVICE ORDERING INFORMATION**

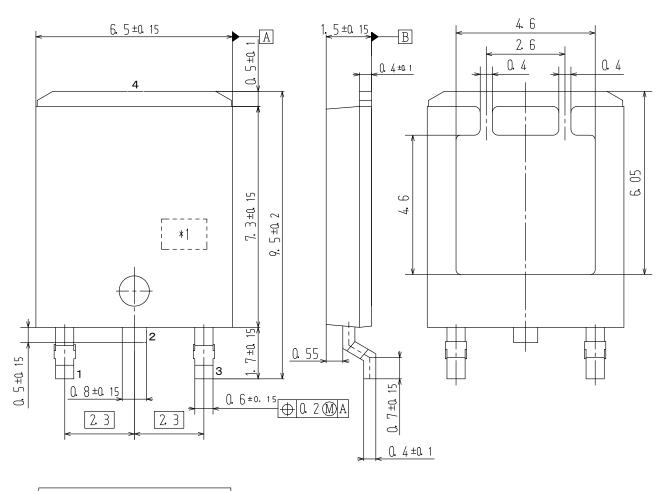
Device	Marking	Package	Shipping <sup>†</sup>
ATP304-TL-H	ATP304	DPAK (Single Gauge) / ATPAK (Pb-Free / Halogen Free)	3000/ Tape & Reel

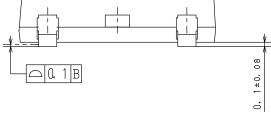
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, <a href="https://example.com/BRD8011/D">BRD8011/D</a>.



#### DPAK (Single Gauge) / ATPAK CASE 369AM ISSUE O

**DATE 29 FEB 2012** 





Pin2 is idle pin with electrical designation only carried

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